1310nm DFB LD Module for Analog application

Features

MQW 1310nm DFB LD

Built-in InGaAsP monitor PD

Built-in optical isolator

Excellent reliability

High Linearity

Low RIN Noise

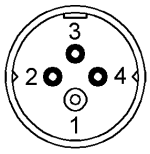
Applications

Mobile communication systems

CATV transmission systems

Analog Transmission

PIN assignment



	F type	S type
1	LD(+)/case	case
2	LD(-)	LD(-)
3	PD(-)	PD(+)
4	PD(+)	LD(+)/PD(-)

Absolute maximum ratings

Parameter	Symbol	Min.	Max.	Unit	Test condition
Storage temperature	Tst	-40	+100	°C	-
Operating temperature	Top	-40	+85	°C	-
Reverse voltage	V_R		2	V	CW
Solder temperature/time			260/10	°C /S	-

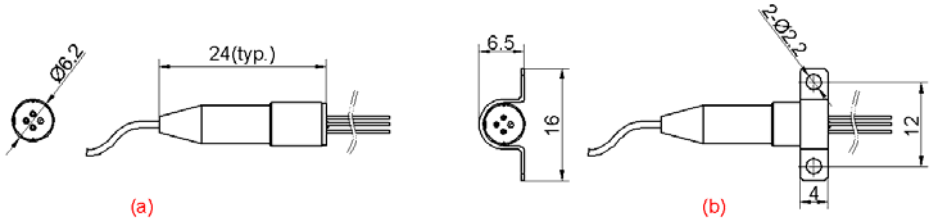
Optical & electrical characteristics(T=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Center wavelength	λc	1290	1310	1330	nm	-
Threshold current	Ith	-	10	15	mA	
Side mode suppression ratio	SMSR	30	40	-	dB	
Spectral width	Δλ	-	1	2	nm	Ith+20mA,-20dB
Output power	P	2	-	-	mW	CW,Ith+20mA
Operating voltage	Vop	-	1.1	1.5	V	CW,Ith+20mA
Rise/ Fall time	Tr/Tf	-	0.3	0.7	nS	10%~90%,Ib=Ith
Monitor current	Im	0.1	0.7	-	mA	CW,Ith+20mA
Optical Isolation①	Iso	30	-	-	dB	Single stage
		50	-	-	dB	Dual stage
Relative Intensity Noise	RIN	-	-145	-	dBc	CW
Second-order distortion②	IMD2			-46	dBc	OMI=20%,2mW
Third-Order Intermodulation	IMD3	-	-65	-60	dBc	OMI=20%,2mW
RF Bandwidth	BW	2300	-	-	MHz	-3dB

Note: ①temperature range:-20~70°C

②CATV return path,2tone (13MHz,19MHz)

Dimensions Diagram



Order information

SLA2	*X*	*X*	*X*	*X*	*X*	*X*
	Isolator	**wavelength**	**PIN out**	**Power**	**BW**	**Package**
	0,no	3,1310	F,F	M, >1mW	1,1G	1, (a)
	1,Single	5,1550	S,S	H, >2mW	2,2.3G	2, (b)
	2,Double	C,CWDM.		U, >4mW		S,spec.